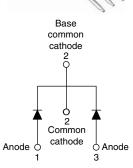


Vishay Semiconductors

HEXFRED® Ultrafast Soft Recovery Diode, 2 x 8 A





TO-220AB

PRODUCT SUMMARY						
Package	TO-220AB					
I _{F(AV)}	2 x 8 A					
V_{R}	600 V					
V _F at I _F	1.7 V					
t _{rr} (typ.)	18 ns					
T _J max.	150 °C					
Diode variation	Common cathode					

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified for industrial level





BENEFITS

- · Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

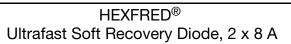
DESCRIPTION

VS-HFA16TA60CPbF is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 8 A per leg continuous current, the VS-HFA16TA60CPbF is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the to portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA16TA60CPbF is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Cathode to anode voltage	V _R		600	V			
Maximum continuous forward current per leg	- I _F	T _C = 100 °C	8	^			
per device			16				
Single pulse forward current	I _{FSM}		60	А			
Maximum repetitive forward current	I _{FRM}		24				
Manifestor and the size of the		T _C = 25 °C	36	147			
Maximum power dissipation	P_{D}	T _C = 100 °C	14	W			
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C			

VS-HFA16TA60CPbF

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ELECTRICAL SPECIFICATIONS PER LEG (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V_{BR}	Ι _R = 100 μΑ		600	-	-	
		I _F = 8 A		-	1.4	1.7	V
Maximum forward voltage	V_{FM}	I _F = 16 A	See fig. 1	-	1.7	2.1	
		I _F = 8 A, T _J = 125 °C		-	1.4	1.7	
Maximum reverse		V _R = V _R rated	Coo fig. 0	-	0.3	5.0	
leakage current	I _{RM}	$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated	See fig. 2	-	100	500	μA
Junction capacitance	C _T	V _R = 200 V	See fig. 3	-	10	25	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body		-	8.0	-	nH

DYNAMIC RECOVERY CHARACTERISTICS PER LEG (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS	
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	18	-	
Reverse recovery time See fig. 5 and 10	t _{rr1}	T _J = 25 °C		-	37	55	ns
Gee lig. 5 and 10	t _{rr2}	T _J = 125 °C		-	55	90	
Peak recovery current	I _{RRM1}	T _J = 25 °C	I _F = 8.0 A	-	3.5	5.0	А
See fig. 6	I _{RRM2}	T _J = 125 °C		-	4.5	8.0	
Reverse recovery charge	Q _{rr1}	T _J = 25 °C	dl _F /dt = 200 A/µs	-	65	138	nC
See fig. 7	Q _{rr2}	T _J = 125 °C	V _R = 200 V	-	124	360	IIC
Peak rate of fall recovery current during t _b See fig. 8	dI _{(rec)M} /dt1	T _J = 25 °C		-	240	-	Δ/
	dI _{(rec)M} /dt2	T _J = 125 °C		-	210	-	A/µs

THERMAL - MECHANICAL SPECIFICATIONS PER LEG							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Junction to case, single leg conducting			-	-	3.5		
Junction to case, both legs conducting	R _{thJC}		-	-	1.75	K/W	
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	- 17/11	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-		
Weight			-	2.0	-	g	
Weight			-	0.07	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-220AB		HFA16	TA60C	•	





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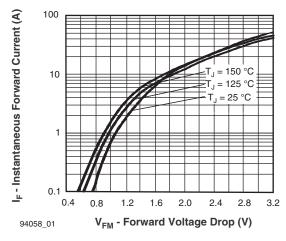


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current (Per Leg)

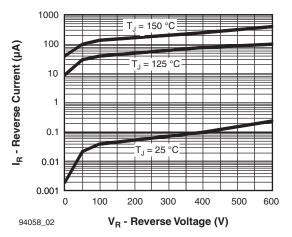


Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Leg)

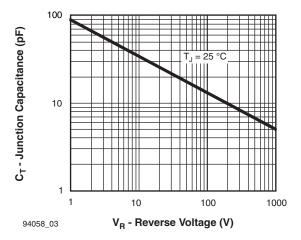


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

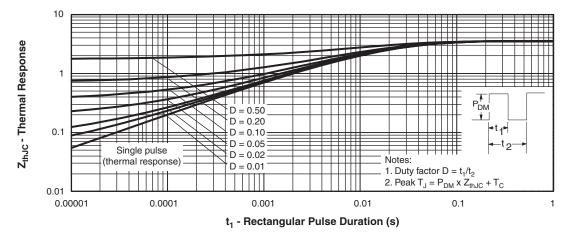


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics (Per Leg)

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HEXFRED® Ultrafast Soft Recovery Diode, 2 x 8 A



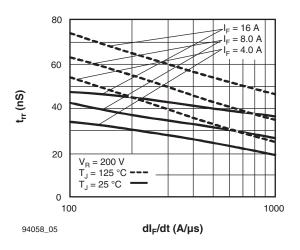


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt (Per Leg)

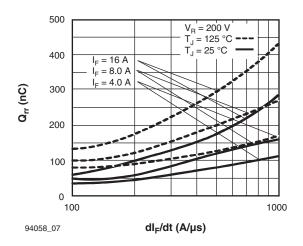


Fig. 7 - Typical Stored Charge vs. dl_F/dt (Per Leg)

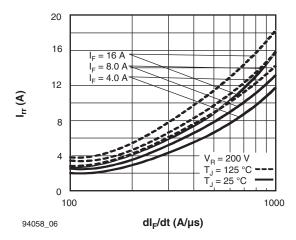


Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)

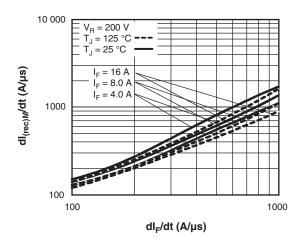


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt (Per Leg)



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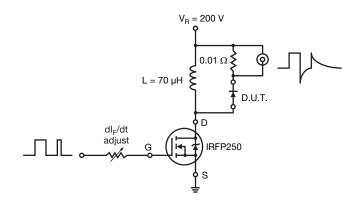
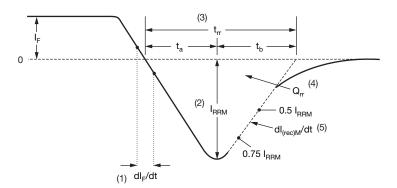


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_E/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during tb portion of tr

Fig. 10 - Reverse Recovery Waveform and Definitions

VS-HFA16TA60CPbF

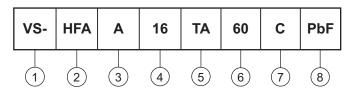
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HEXFRED® Ultrafast Soft Recovery Diode, 2 x 8 A



ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

HEXFRED® family

Electron irradiated

Current rating (16 = 16 A)

Package:

TA = TO-220AB

Voltage rating (60 = 600 V)

Circuit configuration: C = Common cathode

PbF = Lead (Pb)-free 8

Tube standard pack quantity: 50 pieces

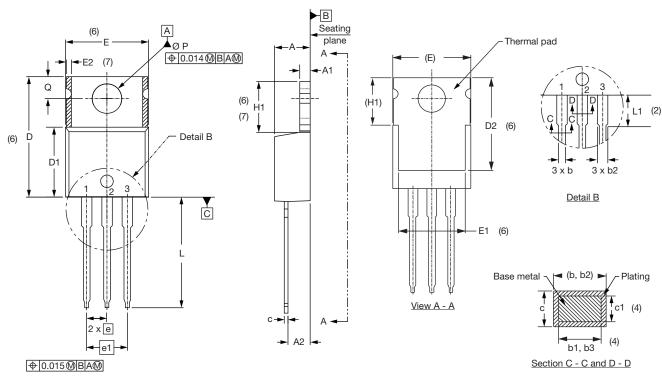
LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?95222					
Part marking information <u>www.vishay.com/doc?95225</u>					



Vishay Semiconductors

TO-220AB

DIMENSIONS in millimeters and inches



Lead assignments

Diodes

- 1. Anode/open
- 2. Cathode
- 3. Anode

Conforms to JEDEC outline TO-220AB

MILLIN	IETERS	INCHES		NOTES
MIN.	MAX.	MIN.	MAX.	NOTES
4.25	4.65	0.167	0.183	
1.14	1.40	0.045	0.055	
2.56	2.92	0.101	0.115	
0.69	1.01	0.027	0.040	
0.38	0.97	0.015	0.038	4
1.20	1.73	0.047	0.068	
1.14	1.73	0.045	0.068	4
0.36	0.61	0.014	0.024	
0.36	0.56	0.014	0.022	4
14.85	15.25	0.585	0.600	3
8.38	9.02	0.330	0.355	
11.68	12.88	0.460	0.507	6
	MIN. 4.25 1.14 2.56 0.69 0.38 1.20 1.14 0.36 0.36 14.85 8.38	4.25 4.65 1.14 1.40 2.56 2.92 0.69 1.01 0.38 0.97 1.20 1.73 1.14 1.73 0.36 0.61 0.36 0.56 14.85 15.25 8.38 9.02	MIN. MAX. MIN. 4.25 4.65 0.167 1.14 1.40 0.045 2.56 2.92 0.101 0.69 1.01 0.027 0.38 0.97 0.015 1.20 1.73 0.047 1.14 1.73 0.045 0.36 0.61 0.014 0.36 0.56 0.014 14.85 15.25 0.585 8.38 9.02 0.330	MIN. MAX. MIN. MAX. 4.25 4.65 0.167 0.183 1.14 1.40 0.045 0.055 2.56 2.92 0.101 0.115 0.69 1.01 0.027 0.040 0.38 0.97 0.015 0.038 1.20 1.73 0.047 0.068 1.14 1.73 0.045 0.068 0.36 0.61 0.014 0.024 0.36 0.56 0.014 0.022 14.85 15.25 0.585 0.600 8.38 9.02 0.330 0.355

SYMBOL	MILLIN	IETERS	INCHES		NOTES
STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° t	o 93°	90° to 93°		
	•				

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline

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Lead tip

Legal Disclaimer Notice



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